



Welcome to [E-XFL.COM](#)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Not For New Designs
Core Processor	M16C/60
Core Size	16-Bit
Speed	24MHz
Connectivity	I ² C, IEBus, UART/USART
Peripherals	DMA, WDT
Number of I/O	85
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LFQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/m30624fgpgp-u9c

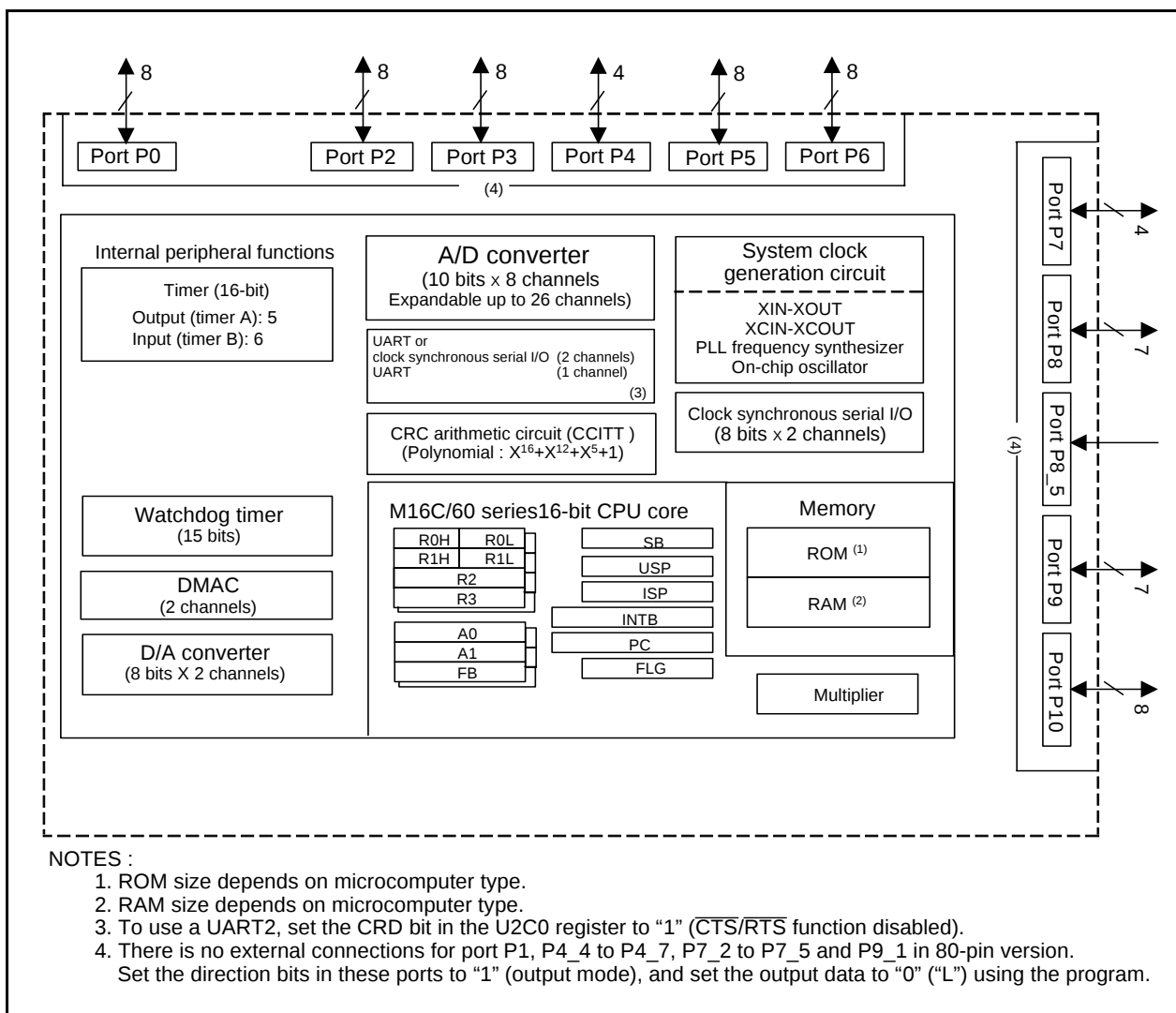


Figure 1.2 M16C/62P Group (M16C/62P, M16C/62PT) 80-pin version Block Diagram

Table 1.6 Product List (3) (T version (M16C/62PT))**As of Dec. 2005**

Type No.	ROM Capacity	RAM Capacity	Package Type ⁽¹⁾	Remarks	
M3062CM6T-XXXFP (D)	48 Kbytes	4 Kbytes	PRQP0100JB-A	Mask ROM version	T Version (High reliability 85°C version)
M3062CM6T-XXXGP (D)			PLQP0100KB-A		
M3062EM6T-XXXGP (P)			PRQP0080JA-A		
M3062CM8T-XXXFP (D)	64 Kbytes	4 Kbytes	PRQP0100JB-A		
M3062CM8T-XXXGP (D)			PLQP0100KB-A		
M3062EM8T-XXXGP (P)			PRQP0080JA-A		
M3062CMAT-XXXFP (D)	96 Kbytes	5 Kbytes	PRQP0100JB-A		
M3062CMAT-XXXGP (D)			PLQP0100KB-A		
M3062EMAT-XXXGP (P)			PRQP0080JA-A		
M3062AMCT-XXXFP (D)	128 Kbytes	10 Kbytes	PRQP0100JB-A		
M3062AMCT-XXXGP (D)			PLQP0100KB-A		
M3062BMCT-XXXGP (P)			PRQP0080JA-A		
M3062CF8TFP (D)	64 K+4 Kbytes	4 Kbytes	PRQP0100JB-A	Flash memory version ⁽²⁾	
M3062CF8TGP			PLQP0100KB-A		
M3062AFCTFP (D)	128K+4 Kbytes	10 Kbytes	PRQP0100JB-A		
M3062AFCTGP (D)			PLQP0100KB-A		
M3062BFCTGP (P)			PRQP0080JA-A		
M3062JFHTFP (D)	384K+4 Kbytes	31 Kbytes	PRQP0100JB-A		
M3062JFHTGP (D)			PLQP0100KB-A		

(D): Under development

(P): Under planning

NOTES:

- The old package type numbers of each package type are as follows.
PRQP0100JB-A : 100P6S-A,
PLQP0100KB-A : 100P6Q-A,
PRQP0080JA-A : 80P6S-A
- In the flash memory version, there is 4K bytes area (block A).

Table 1.8 Product Code of Flash Memory version and ROMless version for M16C/62P

	Product Code	Package	Internal ROM (User ROM Area Without Block A, Block 1)		Internal ROM (Block A, Block 1)		Operating Ambient Temperature
			Program and Erase Endurance	Temperature Range	Program and Erase Endurance	Temperature Range	
Flash memory Version	D3	Lead-included	100	0°C to 60°C	100	0°C to 60°C	-40°C to 85°C
	D5						-20°C to 85°C
	D7		1,000		10,000	-40°C to 85°C	-40°C to 85°C
	D9					-20°C to 85°C	-20°C to 85°C
	U3	Lead-free	100		100	0°C to 60°C	-40°C to 85°C
	U5					-20°C to 85°C	
	U7		1,000		10,000	-40°C to 85°C	-40°C to 85°C
	U9					-20°C to 85°C	-20°C to 85°C
ROM-less version	D3	Lead-included	—	—	—	—	-40°C to 85°C
	D5		—	—	—	—	-20°C to 85°C
	U3	Lead-free	—	—	—	—	-40°C to 85°C
	U5		—	—	—	—	-20°C to 85°C

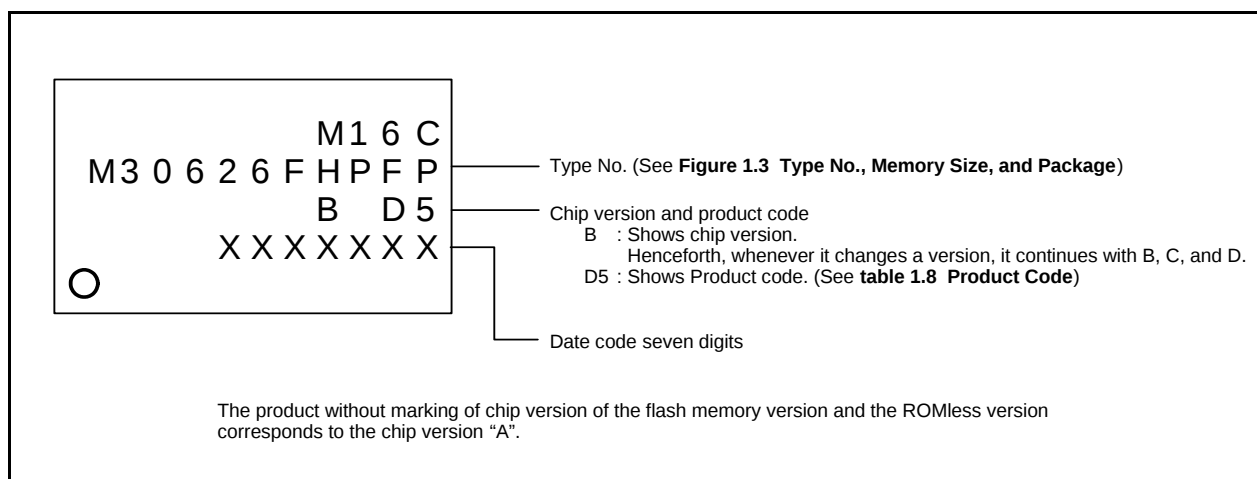
**Figure 1.4 Marking Diagram of Flash Memory version and ROM-less version for M16C/62P (Top View)**

Table 1.11 Pin Characteristics for 128-Pin Package (2)

Pin No.	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
51		P5_6					ALE
52		P5_5					$\overline{\text{HOLD}}$
53		P5_4					$\overline{\text{HLDA}}$
54		P13_3					
55		P13_2					
56		P13_1					
57		P13_0					
58		P5_3					BCLK
59		P5_2					$\overline{\text{RD}}$
60		P5_1					$\overline{\text{WRH/BHE}}$
61		P5_0					$\overline{\text{WRL/WR}}$
62		P12_7					
63		P12_6					
64		P12_5					
65		P4_7					$\overline{\text{CS3}}$
66		P4_6					$\overline{\text{CS2}}$
67		P4_5					$\overline{\text{CS1}}$
68		P4_4					$\overline{\text{CS0}}$
69		P4_3					A19
70		P4_2					A18
71		P4_1					A17
72		P4_0					A16
73		P3_7					A15
74		P3_6					A14
75		P3_5					A13
76		P3_4					A12
77		P3_3					A11
78		P3_2					A10
79		P3_1					A9
80		P12_4					
81		P12_3					
82		P12_2					
83		P12_1					
84		P12_0					
85	VCC2						
86		P3_0					A8(/D7)
87	VSS						
88		P2_7				AN2_7	A7(/D7/D6)
89		P2_6				AN2_6	A6(/D6/D5)
90		P2_5				AN2_5	A5(/D5/D4)
91		P2_4				AN2_4	A4(/D4/D3)
92		P2_3				AN2_3	A3(/D3/D2)
93		P2_2				AN2_2	A2(/D2/D1)
94		P2_1				AN2_1	A1(/D1/D0)
95		P2_0				AN2_0	A0(/D0/-)
96		P1_7	$\overline{\text{INT5}}$				D15
97		P1_6	$\overline{\text{INT4}}$				D14
98		P1_5	$\overline{\text{INT3}}$				D13
99		P1_4					D12
100		P1_3					D11

Table 1.13 Pin Characteristics for 100-Pin Package (1)

Pin No.		Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
FP	GP							
1	99		P9_6			SOUT4	ANEX1	
2	100		P9_5			CLK4	ANEX0	
3	1		P9_4		TB4IN		DA1	
4	2		P9_3		TB3IN		DA0	
5	3		P9_2		TB2IN	SOUT3		
6	4		P9_1		TB1IN	SIN3		
7	5		P9_0		TB0IN	CLK3		
8	6	BYTE						
9	7	CNVSS						
10	8	XCIN	P8_7					
11	9	XCOUT	P8_6					
12	10	RESET						
13	11	XOUT						
14	12	VSS						
15	13	XIN						
16	14	VCC1						
17	15		P8_5	NMI				
18	16		P8_4	INT2	ZP			
19	17		P8_3	INT1				
20	18		P8_2	INT0				
21	19		P8_1		TA4IN/U			
22	20		P8_0		TA4OUT/U			
23	21		P7_7		TA3IN			
24	22		P7_6		TA3OUT			
25	23		P7_5		TA2IN/W			
26	24		P7_4		TA2OUT/W			
27	25		P7_3		TA1IN/V	CTS2/RTS2		
28	26		P7_2		TA1OUT/V	CLK2		
29	27		P7_1		TA0IN/TB5IN	RXD2/SCL2		
30	28		P7_0		TA0OUT	TXD2/SDA2		
31	29		P6_7			TXD1/SDA1		
32	30		P6_6			RXD1/SCL1		
33	31		P6_5			CLK1		
34	32		P6_4			CTS1/RTS1/CTS0/CLKS1		
35	33		P6_3			TXD0/SDA0		
36	34		P6_2			RXD0/SCL0		
37	35		P6_1			CLK0		
38	36		P6_0			CTS0/RTS0		
39	37		P5_7					RDY/CLKOUT
40	38		P5_6					ALE
41	39		P5_5					HOLD
42	40		P5_4					HLAD
43	41		P5_3					BCLK
44	42		P5_2					RD
45	43		P5_1					WRH/BHE
46	44		P5_0					WRL/WR
47	45		P4_7					CS3
48	46		P4_6					CS2
49	47		P4_5					CS1
50	48		P4_4					CS0

Table 1.14 Pin Characteristics for 100-Pin Package (2)

Pin No.		Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
FP	GP							
51	49		P4_3					A19
52	50		P4_2					A18
53	51		P4_1					A17
54	52		P4_0					A16
55	53		P3_7					A15
56	54		P3_6					A14
57	55		P3_5					A13
58	56		P3_4					A12
59	57		P3_3					A11
60	58		P3_2					A10
61	59		P3_1					A9
62	60	VCC2						
63	61		P3_0					A8(/-D7)
64	62	VSS						
65	63		P2_7				AN2_7	A7(/D7/D6)
66	64		P2_6				AN2_6	A6(/D6/D5)
67	65		P2_5				AN2_5	A5(/D5/D4)
68	66		P2_4				AN2_4	A4(/D4/D3)
69	67		P2_3				AN2_3	A3(/D3/D2)
70	68		P2_2				AN2_2	A2(/D2/D1)
71	69		P2_1				AN2_1	A1(/D1/D0)
72	70		P2_0				AN2_0	A0(/D0/-)
73	71		P1_7	INT5				D15
74	72		P1_6	INT4				D14
75	73		P1_5	INT3				D13
76	74		P1_4					D12
77	75		P1_3					D11
78	76		P1_2					D10
79	77		P1_1					D9
80	78		P1_0					D8
81	79		P0_7				AN0_7	D7
82	80		P0_6				AN0_6	D6
83	81		P0_5				AN0_5	D5
84	82		P0_4				AN0_4	D4
85	83		P0_3				AN0_3	D3
86	84		P0_2				AN0_2	D2
87	85		P0_1				AN0_1	D1
88	86		P0_0				AN0_0	D0
89	87		P10_7	KI3			AN7	
90	88		P10_6	KI2			AN6	
91	89		P10_5	KI1			AN5	
92	90		P10_4	KI0			AN4	
93	91		P10_3				AN3	
94	92		P10_2				AN2	
95	93		P10_1				AN1	
96	94	AVSS						
97	95		P10_0				AN0	
98	96	VREF						
99	97	AVCC						
100	98		P9_7			SIN4	ADTRG	

Table 1.16 Pin Characteristics for 80-Pin Package (2)

Pin No.	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
51		P3_0					
52		P2_7				AN2_7	
53		P2_6				AN2_6	
54		P2_5				AN2_5	
55		P2_4				AN2_4	
56		P2_3				AN2_3	
57		P2_2				AN2_2	
58		P2_1				AN2_1	
59		P2_0				AN2_0	
60		P0_7				AN0_7	
61		P0_6				AN0_6	
62		P0_5				AN0_5	
63		P0_4				AN0_4	
64		P0_3				AN0_3	
65		P0_2				AN0_2	
66		P0_1				AN0_1	
67		P0_0				AN0_0	
68		P10_7	KI3			AN7	
69		P10_6	KI2			AN6	
70		P10_5	KI1			AN5	
71		P10_4	KI0			AN4	
72		P10_3				AN3	
73		P10_2				AN2	
74		P10_1				AN1	
75	AVSS						
76		P10_0				AN0	
77	VREF						
78	AVCC						
79		P9_7			SIN4	ADTRG	
80		P9_6			SOUT4	ANEX1	

Table 1.21 Pin Description (80-pin Version) (2)

Signal Name	Pin Name	I/O Type	Power Supply ⁽¹⁾	Description
Reference voltage input	VREF	I	VCC1	Applies the reference voltage for the A/D converter and D/A converter.
A/D converter	AN0 to AN7, AN0_0 to AN0_7, AN2_0 to AN2_7	I	VCC1	Analog input pins for the A/D converter.
	ADTRG	I	VCC1	This is an A/D trigger input pin.
	ANEX0	I/O	VCC1	This is the extended analog input pin for the A/D converter, and is the output in external op-amp connection mode.
	ANEX1	I	VCC1	This is the extended analog input pin for the A/D converter.
D/A converter	DA0, DA1	O	VCC1	This is the output pin for the D/A converter.
I/O port ⁽¹⁾	P0_0 to P0_7, P2_0 to P2_7, P3_0 to P3_7, P5_0 to P5_7, P6_0 to P6_7, P10_0 to P10_7	I/O	VCC1	8-bit I/O ports in CMOS, having a direction register to select an input or output. Each pin is set as an input port or output port. An input port can be set for a pull-up or for no pull-up in 4-bit unit by program.
	P8_0 to P8_4, P8_6, P8_7, P9_0, P9_2 to P9_7	I/O	VCC1	I/O ports having equivalent functions to P0.
	P4_0 to P4_3, P7_0, P7_1, P7_6, P7_7	I/O	VCC1	I/O ports having equivalent functions to P0. (however, output of P7_0 and P7_1 for the N-channel open drain output.)
Input port	P8_5	I	VCC1	Input pin for the $\overline{\text{NMI}}$ interrupt. Pin states can be read by the P8_5 bit in the P8 register.

I : Input O : Output I/O : Input and output

NOTES:

1. There is no external connections for port P1, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version. Set the direction bits in these ports to "1" (output mode), and set the output data to "0" ("L") using the program.

2.8.8 Stack Pointer Select Flag (U Flag)

ISP is selected when the U flag is “0”; USP is selected when the U flag is “1”.

The U flag is cleared to “0” when a hardware interrupt request is accepted or an INT instruction for software interrupt Nos. 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is configured with three bits, for specification of up to eight processor interrupt priority levels from level 0 to level 7.

If a requested interrupt has priority greater than IPL, the interrupt is enabled.

2.8.10 Reserved Area

When write to this bit, write “0”. When read, its content is indeterminate.

Table 5.3 Recommended Operating Conditions (2) ⁽¹⁾

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
f(XIN)	Main Clock Input Oscillation Frequency ⁽²⁾	VCC1=3.0V to 5.5V	0		16	MHz
		VCC1=2.7V to 3.0V	0		20×VCC1 –44	MHz
f(XCIN)	Sub-Clock Oscillation Frequency			32.768	50	kHz
f(Ring)	On-chip Oscillation Frequency		0.5	1	2	MHz
f(PLL)	PLL Clock Oscillation Frequency ⁽²⁾	VCC1=3.0V to 5.5V	10		24	MHz
		VCC1=2.7V to 3.0V	10		46.67×VCC1 –116	MHz
f(BCLK)	CPU Operation Clock		0		24	MHz
tsu(PLL)	PLL Frequency Synthesizer Stabilization Wait Time	VCC1=5.5V			20	ms
		VCC1=3.0V			50	ms

NOTES:

1. Referenced to VCC1 = VCC2 = 2.7 to 5.5V at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified.
2. Relationship between main clock oscillation frequency, and supply voltage.

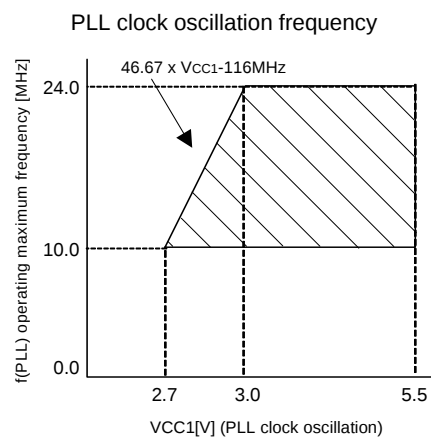
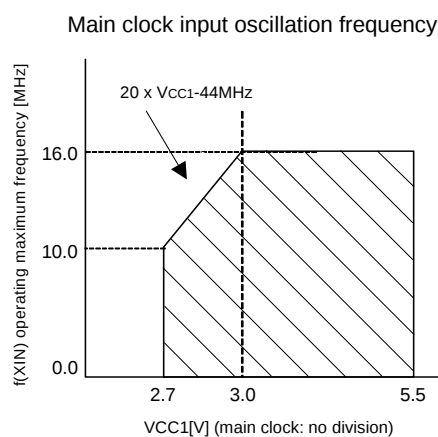


Table 5.6 Flash Memory Version Electrical Characteristics ⁽¹⁾ for 100 cycle products (D3, D5, U3, U5)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance ⁽³⁾		100			cycle
–	Word Program Time (Vcc1=5.0V)			25	200	μs
–	Lock Bit Program Time			25	200	μs
–	Block Erase Time (Vcc1=5.0V)	4-Kbyte block		0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
–	Erase All Unlocked Blocks Time ⁽²⁾				4×n	s
tps	Flash Memory Circuit Stabilization Wait Time				15	μs
–	Data Hold Time ⁽⁵⁾		10			year

Table 5.7 Flash Memory Version Electrical Characteristics ⁽⁶⁾ for 10,000 cycle products (D7, D9, U7, U9) (Block A and Block 1 ⁽⁷⁾)

Symbol	Parameter	Standard			Unit
		Min.	Typ.	Max.	
—	Program and Erase Endurance ^(3, 8, 9)	10,000 ⁽⁴⁾			cycle
—	Word Program Time (V _{CC1} =5.0V)		25		μs
—	Lock Bit Program Time		25		μs
—	Block Erase Time (V _{CC1} =5.0V)	4-Kbyte block		0.3	s
t _{PS}	Flash Memory Circuit Stabilization Wait Time			15	μs
—	Data Hold Time ⁽⁵⁾	10			year

NOTES:

1. Referenced to V_{CC1}=4.5 to 5.5V, 3.0 to 3.6V at T_{opr} = 0 to 60 °C (D3, D5, U3, U5) unless otherwise specified.
2. n denotes the number of block erases.
3. Program and Erase Endurance refers to the number of times a block erase can be performed.
If the program and erase endurance is n (n=100, 1,000, or 10,000), each block can be erased n times.
For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
4. Maximum number of E/W cycles for which operation is guaranteed.
5. T_{opr} = -40 to 85 °C (D3, D7, U3, U7) / -20 to 85 °C (D5, D9, U5, U9).
6. Referenced to V_{CC1} = 4.5 to 5.5V, 3.0 to 3.6V at T_{opr} = -40 to 85 °C (D7, U7) / -20 to 85 °C (D9, U9) unless otherwise specified.
7. Table 5.7 applies for block A or block 1 program and erase endurance > 1,000. Otherwise, use Table 5.6.
8. To reduce the number of program and erase endurance when working with systems requiring numerous rewrites, write to unused word addresses within the block instead of rewrite. Erase block only after all possible addresses are used. For example, an 8-word program can be written 256 times maximum before erase becomes necessary. Maintaining an equal number of erasure between block A and block 1 will also improve efficiency. It is important to track the total number of times erasure is used.
9. Should erase error occur during block erase, attempt to execute clear status register command, then block erase command at least three times until erase error disappears.
10. Set the PM17 bit in the PM1 register to "1" (wait state) when executing more than 100 times rewrites (D7, D9, U7 and U9).
11. Customers desiring E/W failure rate information should contact their Renesas technical support representative.

Table 5.8 Flash Memory Version Program / Erase Voltage and Read Operation Voltage Characteristics (at T_{opr} = 0 to 60 °C(D3, D5, U3, U5), T_{opr} = -40 to 85 °C(D7, U7) / T_{opr} = -20 to 85 °C(D9, U9))

Flash Program, Erase Voltage	Flash Read Operation Voltage
V _{CC1} = 3.3 V ± 0.3 V or 5.0 V ± 0.5 V	V _{CC1} =2.7 to 5.5 V

$$V_{CC1}=V_{CC2}=5V$$

Timing Requirements

($V_{CC1} = V_{CC2} = 5V$, $V_{SS} = 0V$, at $T_{opr} = -20$ to $85^{\circ}C$ / -40 to $85^{\circ}C$ unless otherwise specified)

Table 5.15 Timer A Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	100		ns
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	40		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	40		ns

Table 5.16 Timer A Input (Gating Input in Timer Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	400		ns
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	200		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	200		ns

Table 5.17 Timer A Input (External Trigger Input in One-shot Timer Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	200		ns
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	100		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	100		ns

Table 5.18 Timer A Input (External Trigger Input in Pulse Width Modulation Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(TAH)}$	TAiIN Input HIGH Pulse Width	100		ns
$t_{w(TAL)}$	TAiIN Input LOW Pulse Width	100		ns

Table 5.19 Timer A Input (Counter Increment/Decrement Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(UP)}$	TAiOUT Input Cycle Time	2000		ns
$t_{w(UPH)}$	TAiOUT Input HIGH Pulse Width	1000		ns
$t_{w(UPL)}$	TAiOUT Input LOW Pulse Width	1000		ns
$t_{su(UP-TIN)}$	TAiOUT Input Setup Time	400		ns
$t_{h(TIN-UP)}$	TAiOUT Input Hold Time	400		ns

Table 5.20 Timer A Input (Two-phase Pulse Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN Input Cycle Time	800		ns
$t_{su(TAIN-TAOUT)}$	TAiOUT Input Setup Time	200		ns
$t_{su(TAOUT-TAIN)}$	TAiIN Input Setup Time	200		ns

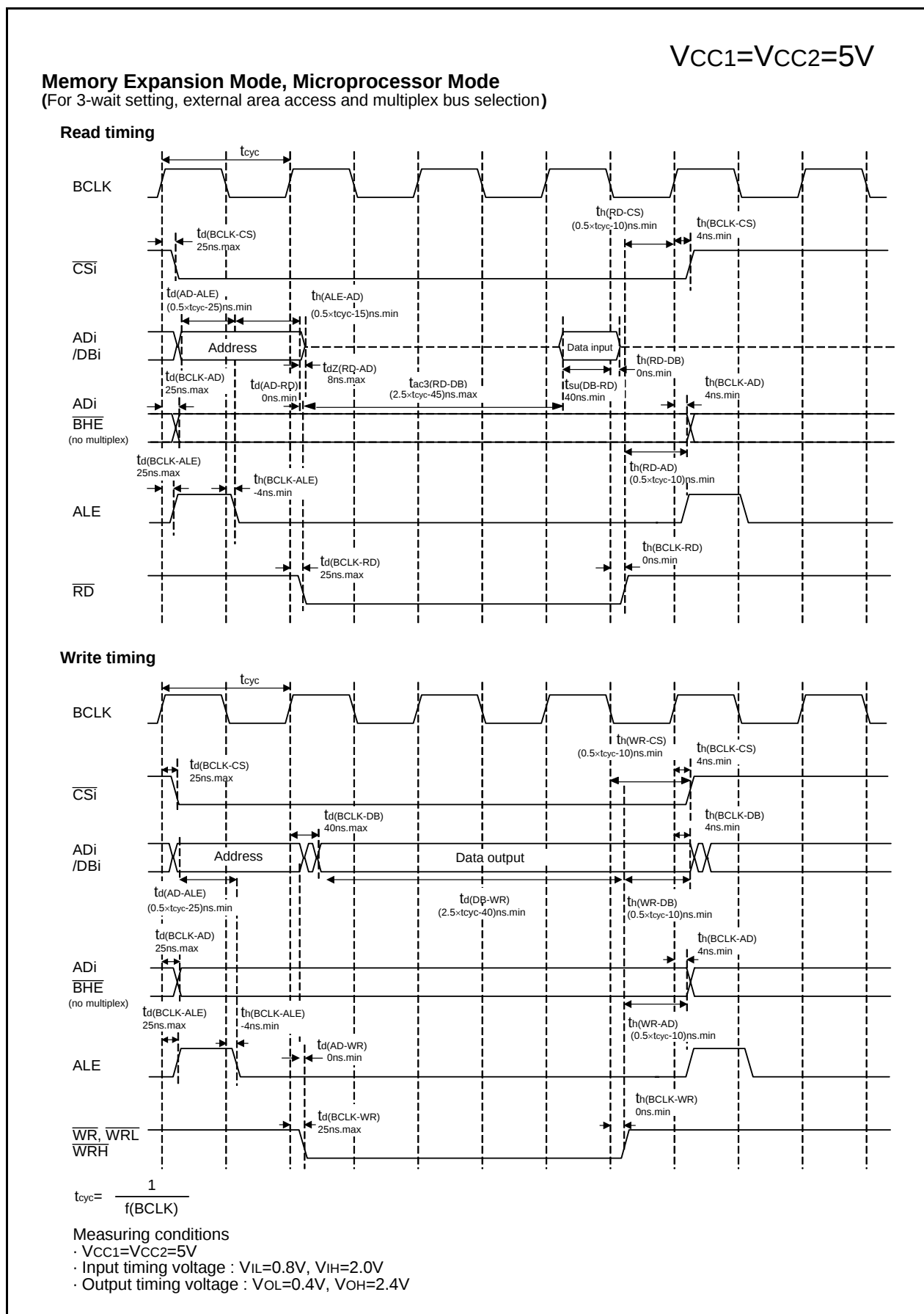


Figure 5.11 Timing Diagram (9)

$$V_{CC1}=V_{CC2}=3V$$

Table 5.30 Electrical Characteristics (1) (1)

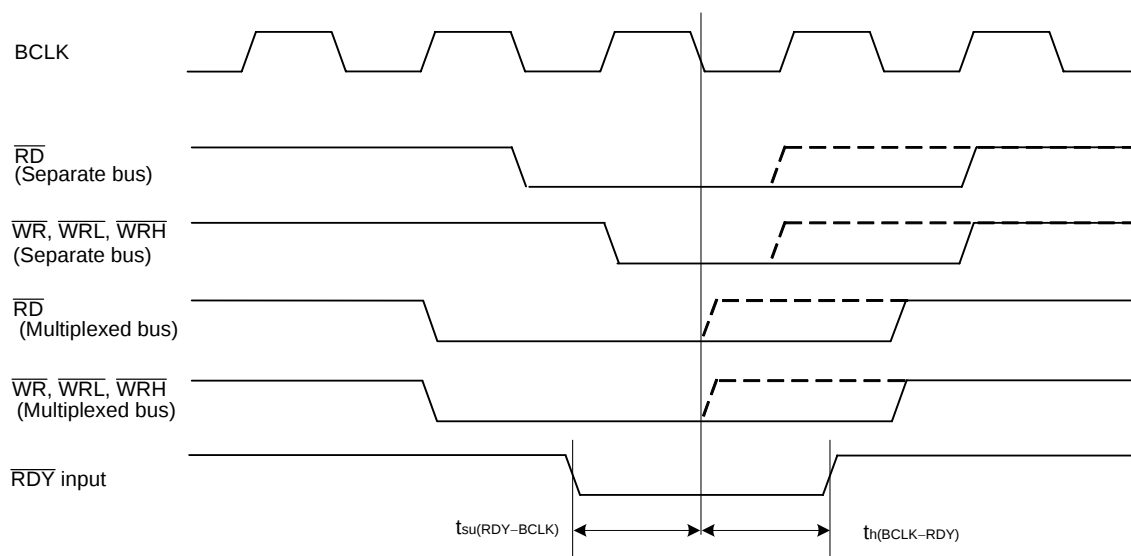
Symbol	Parameter		Measuring Condition	Standard			Unit
				Min.	Typ.	Max.	
VOH	HIGH Output Voltage (3)	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	IOH=−1mA	VCC1−0.5		VCC1	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	IOH=−1mA (2)	VCC2−0.5		VCC2	
VOH	HIGH Output Voltage XOUT	HIGHPOWER	IOH=−0.1mA	VCC1−0.5		VCC1	V
		LOWPOWER	IOH=−50μA	VCC1−0.5		VCC1	
	HIGH Output Voltage XCOUT	HIGHPOWER	With no load applied		2.5		V
		LOWPOWER	With no load applied		1.6		
VOL	LOW Output Voltage (3)	P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	IOL=1mA			0.5	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	IOL=1mA (2)			0.5	
VOL	LOW Output Voltage XOUT	HIGHPOWER	IOL=0.1mA			0.5	V
		LOWPOWER	IOL=50μA			0.5	
	LOW Output Voltage XCOUT	HIGHPOWER	With no load applied		0		V
		LOWPOWER	With no load applied		0		
VT+−VT−	Hysteresis	HOLD, RDY, TA0IN to TA4IN, TBOIN to TB5IN, INT0 to INT5, NMI, ADTRG, CTS0 to CTS2, CLK0 to CLK4, TA0OUT to TA4OUT, KI0 to KI3, RXD0 to RXD2, SCL0 to SCL2, SDA0 to SDA2, SIN3, SIN4		0.2		0.8	V
VT+−VT−	Hysteresis	RESET		0.2	(0.7)	1.8	V
IiH	HIGH Input Current (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, RESET, CNVSS, BYTE	VI=3V			4.0	μA
IiL	LOW Input Current (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, RESET, CNVSS, BYTE	VI=0V			−4.0	μA
RPULLUP	Pull-Up Resistance (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1	VI=0V	50	100	500	kΩ
RfXIN	Feedback Resistance XIN				3.0		MΩ
RfXCIN	Feedback Resistance XCIN				25		MΩ
VRAM	RAM Retention Voltage		At stop mode	2.0			V

NOTES:

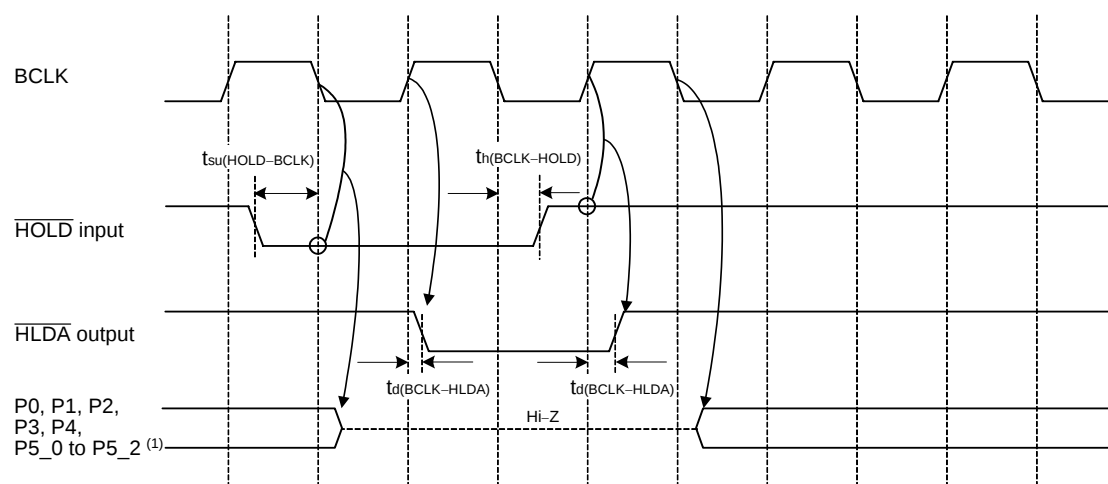
1. Referenced to VCC1 = VCC2 = 2.7 to 3.3V, VSS = 0V at Topr = −20 to 85°C / −40 to 85°C, f(XIN)=10MHz no wait unless otherwise specified.
2. VCC1 for the port P6 to P11 and P14, and VCC2 for the port P0 to P5 and P12 to P13
3. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

Memory Expansion Mode, Microprocessor Mode

(Effective for setting with wait)

 $V_{CC1}=V_{CC2}=3V$ 

(Common to setting with wait and setting without wait)

**NOTES:**

1. These pins are set to high-impedance regardless of the input level of the BYTE pin, PM06 bit in PM0 register and PM11 bit in PM1 register.

Measuring conditions :

- $V_{CC1}=V_{CC2}=3V$
- Input timing voltage : Determined with $V_{IL}=0.6V$, $V_{IH}=2.4V$
- Output timing voltage : Determined with $V_{OL}=1.5V$, $V_{OH}=1.5V$

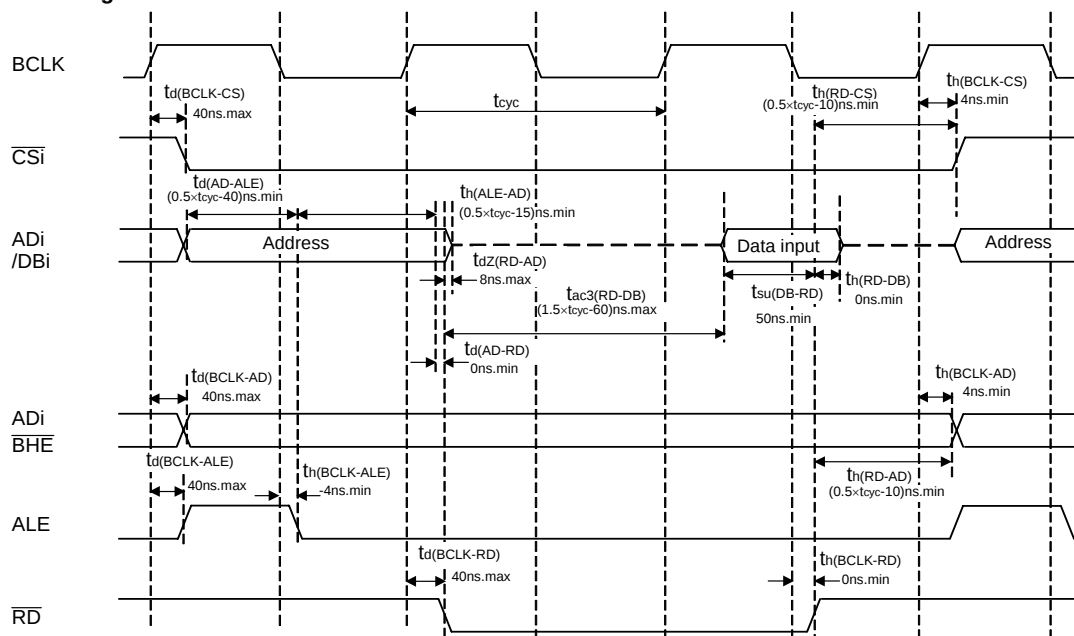
Figure 5.15 Timing Diagram (3)

Memory Expansion Mode, Microprocessor Mode

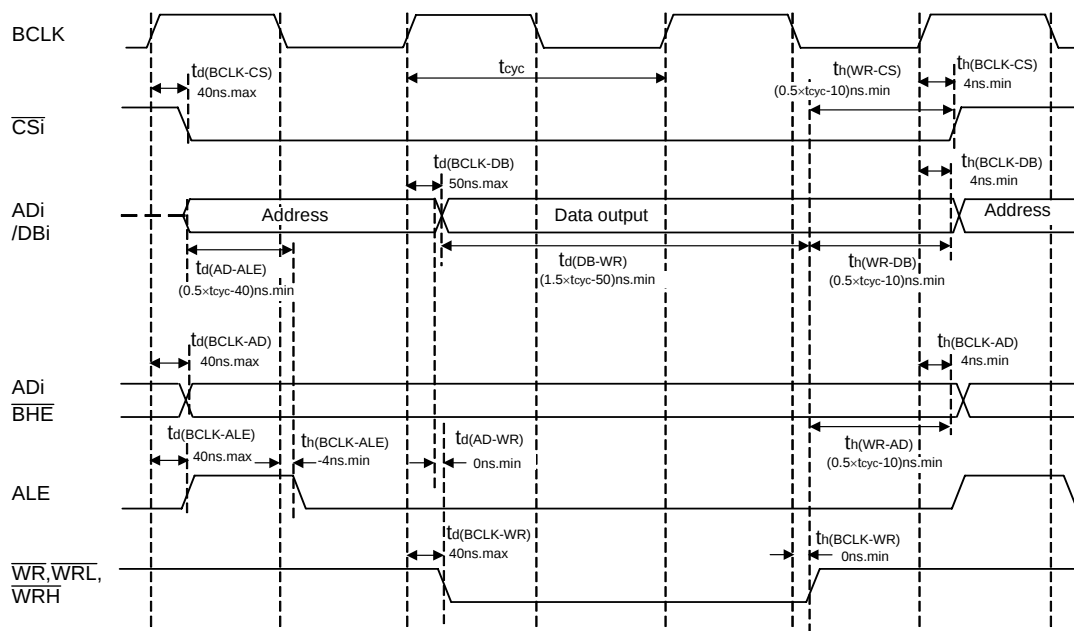
(For 2-wait setting, external area access and multiplex bus selection)

 $V_{CC1}=V_{CC2}=3V$

Read timing



Write timing



$$t_{\text{cyc}} = \frac{1}{f(\text{BCLK})}$$

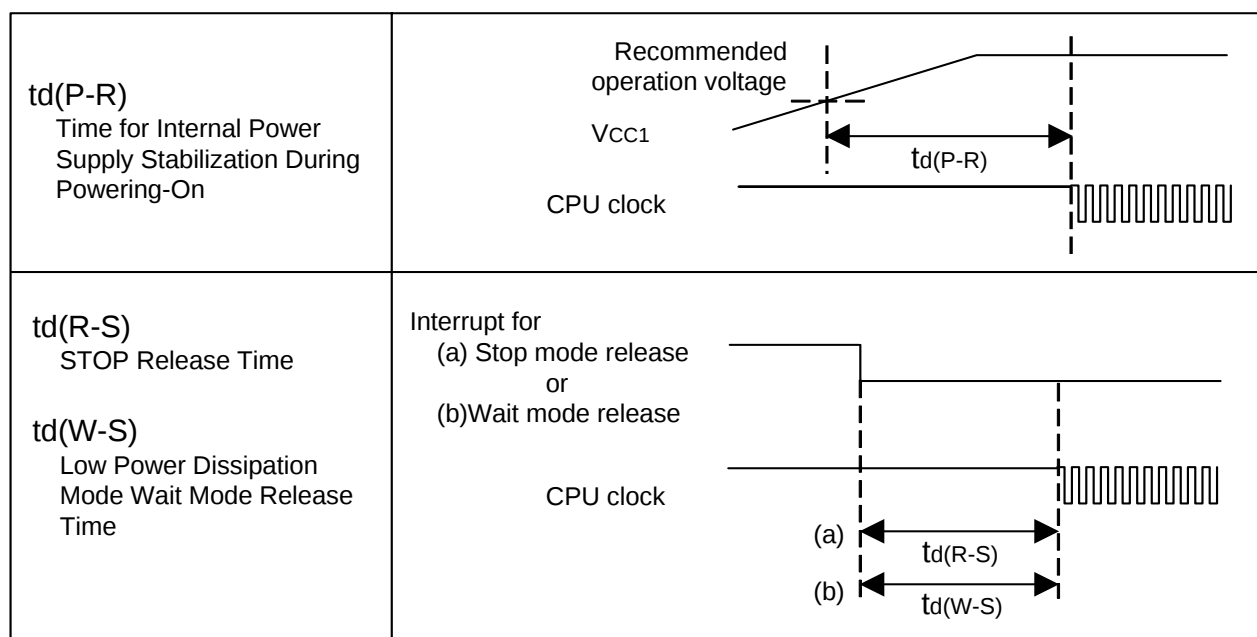
Measuring conditions

- $V_{CC1}=V_{CC2}=3V$
- Input timing voltage : $V_{IL}=0.6V$, $V_{IH}=2.4V$
- Output timing voltage : $V_{OL}=1.5V$, $V_{OH}=1.5V$

Figure 5.20 Timing Diagram (8)

Table 5.56 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for Internal Power Supply Stabilization During Powering-On	$V_{CC1}=4.0V$ to $5.5V$			2	ms
$t_{d(R-S)}$	STOP Release Time				150	μs
$t_{d(W-S)}$	Low Power Dissipation Mode Wait Mode Release Time				150	μs

**Figure 5.22 Power Supply Circuit Timing Diagram**

$$V_{CC1}=V_{CC2}=5V$$

Timing Requirements

($V_{CC1} = V_{CC2} = 5V$, $V_{SS} = 0V$, at $T_{opr} = -40$ to $85^{\circ}C$ (T version) / -40 to $125^{\circ}C$ (V version) unless otherwise specified)

Table 5.66 Timer B Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on one edge)	100		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on one edge)	40		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on one edge)	40		ns
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on both edges)	200		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on both edges)	80		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on both edges)	80		ns

Table 5.67 Timer B Input (Pulse Period Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	400		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	200		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	200		ns

Table 5.68 Timer B Input (Pulse Width Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	400		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	200		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	200		ns

Table 5.69 A/D Trigger Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(AD)}$	$\overline{ADTRG}$ Input Cycle Time	1000		ns
$t_{w(ADL)}$	$\overline{ADTRG}$ input LOW Pulse Width	125		ns

Table 5.70 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi Input Cycle Time	200		ns
$t_{w(CKH)}$	CLKi Input HIGH Pulse Width	100		ns
$t_{w(CKL)}$	CLKi Input LOW Pulse Width	100		ns
$t_{d(C-Q)}$	TXDi Output Delay Time		80	ns
$t_{h(C-Q)}$	TXDi Hold Time	0		ns
$t_{su(D-C)}$	RXDi Input Setup Time	70		ns
$t_{h(C-D)}$	RXDi Input Hold Time	90		ns

Table 5.71 External Interrupt $\overline{INTi}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{INTi}$ Input HIGH Pulse Width	250		ns
$t_{w(INL)}$	$\overline{INTi}$ Input LOW Pulse Width	250		ns

REVISION HISTORY		M16C/62P Group (M16C/62P, M16C/62PT) Hardware Manual	
Rev.	Date	Description	
		Page	Summary
		40	Table 5.24 is partly revised.
		57	Table 5.43 is partly revised.
		70	Table 5.48 is partly revised.
		72	Table 5.50 is partly revised.
		73	Table 5.53 is partly revised.
		74	Table 5.55 is revised.
		76	Table 5.57 is partly revised.
		79	Table 5.69 is partly revised.
2.41	Jan 01, 2006	-	voltage down detection reset -> brown-out detection Reset
		2-4	Tables 1.1 to 1.3 Performance outline of M16C/62P group are partly revised.
		7	Table 1.4 Product List (1) is partly revised. Note 1 is added.
		8	Table 1.5 Product List (2) is partly revised. Note 1, 2 and 3 are added.
		9	Table 1.6 Product List (3) is partly revised. Note 1 and 2 are added.
		10	Table 1.7 Product List (4) is partly revised. Note 1 and 2 are added.
		11	Figure 1.3 Type No., Memory Size, Shows RAM capacity, and Package is partly revised
		12	Table 1.8 Product Code of Flash Memory version and ROMless version for M16C/62P is partly revised.
		13	Table 1.9 Product Code of Flash Memory version for M16C/62P is partly revised.
		14	Figure 1.6 Pin Configuration (Top View) is partly revised.
		15-17	Tables 1.10 to 1.12 Pin Characteristics for 128-Pin Package are added.
		18-19	Figure 1.7 and 1.8 Pin Configuration (Top View) are partly revised.
		20-21	Tables 1.13 to 1.14 Pin Characteristics for 100-Pin Package are added.
		22	Figure 1.9 Pin Configuration (Top View) is partly revised.
		23-24	Tables 1.15 to 1.16 Pin Characteristics for 80-Pin Package are added.
		25-29	Tables 1.17 to 1.21 are partly revised.
		34	Note 4 of Table 4.1 SFR Information is partly revised.
		43	Table 5.4 A/D Conversion Characteristics is partly revised.
		45	Table 5.6 Flash Memory Version Electrical Characteristics for 100 cycle products is partly revised. Table 5.7 Flash Memory Version Electrical Characteristics for 10,000 cycle products is partly revised. Table 5.8 Flash Memory Version Program / Erase Voltage and Read Operation Voltage Characteristics is partly revised.
		46	Table 5.9 Low Voltage Detection Circuit Electrical Characteristics is partly revised.

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Keep safety first in your circuit designs!

1. Renesas Technology Corp. puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corp. product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corp. or a third party.
2. Renesas Technology Corp. assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corp. without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor for the latest product information before purchasing a product listed herein.
The information described here may contain technical inaccuracies or typographical errors.
Renesas Technology Corp. assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
Please also pay attention to information published by Renesas Technology Corp. by various means, including the Renesas Technology Corp. Semiconductor home page (<http://www.renesas.com>).
4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corp. assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
5. Renesas Technology Corp. semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
6. The prior written approval of Renesas Technology Corp. is necessary to reprint or reproduce in whole or in part these materials.
7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
8. Please contact Renesas Technology Corp. for further details on these materials or the products contained therein.



RENESAS SALES OFFICES

<http://www.renesas.com>

Refer to "<http://www.renesas.com/en/network>" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510